

Description

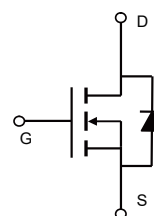
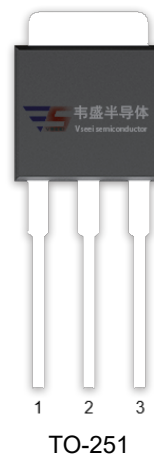
The VSM60N04 uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = 40V, I_D = 60A$
 $R_{DS(ON)} < 7.5m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 15m\Omega @ V_{GS} = 4.5V$
- High density cell design for ultra low $R_{DS(ON)}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Load switching
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VSM60N04	VSM60N04-T1	TO-251	-	-	-

Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	60	A
Drain Current-Continuous($T_c = 100^\circ C$)	$I_D(100^\circ C)$	42	A
Pulsed Drain Current	I_{DM}	200	A
Maximum Power Dissipation	P_D	65	W
Derating factor		0.43	W/ $^\circ C$
Single pulse avalanche energy (Note 5)	E_{AS}	219	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ C$

Thermal Characteristic

Thermal Resistance,Junction-to-Case	$R_{\theta JC}$	2.3	$^{\circ}C/W$
Thermal Resistance,Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	60	$^{\circ}C/W$

Electrical Characteristics ($T_C=25^{\circ}C$ unless otherwise noted)

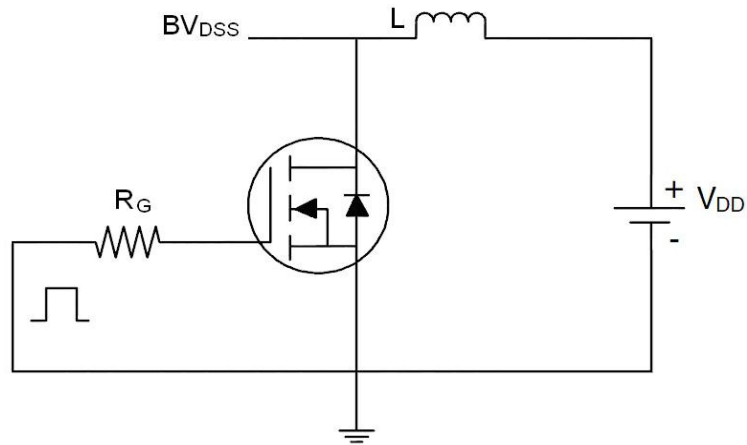
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	40	45	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =20A	-	5.8	7.5	mΩ
		V _{GS} =4.5V, I _D =20A		11	15	
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =20A	15	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	1800	-	pF
Output Capacitance	C _{OSS}		-	187	-	pF
Reverse Transfer Capacitance	C _{rSS}		-	150	-	pF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, I _D =2A, R _L =1Ω V _{GS} =10V, R _G =3Ω	-	6.4	-	nS
Turn-on Rise Time	t _r		-	17.2	-	nS
Turn-Off Delay Time	t _{d(off)}		-	29.6	-	nS
Turn-Off Fall Time	t _f		-	16.8	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =20A, V _{GS} =10V	-	35.6		nC
Gate-Source Charge	Q _{gs}		-	5.4		nC
Gate-Drain Charge	Q _{gd}		-	9.8		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =10A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	60	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 20A di/dt = 100A/μs(Note3)	-	29	-	nS
Reverse Recovery Charge	Q _{rr}		-	26	-	nC
Forward Turn-On Time	t _{on}	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

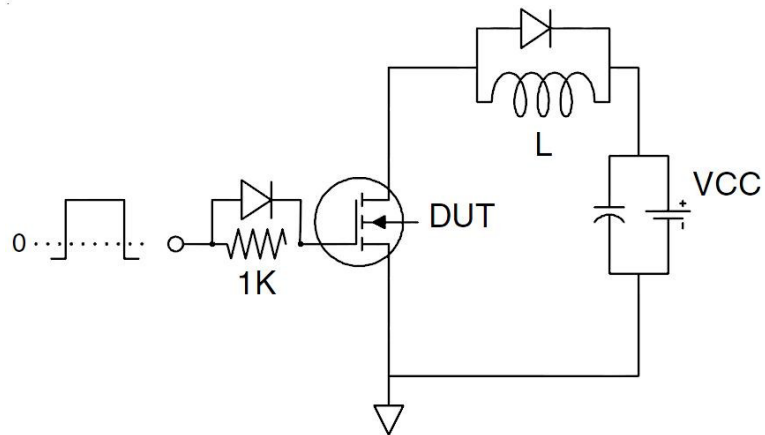
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}C$. The value in any given application depends on the user's specific board design, and the maximum temperature of $150^{\circ}C$ may be used if the PCB allows it. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. E_{AS} condition : $T_J=25^{\circ}C, V_{DD}=20V, V_G=10V, L=1mH, R_g=25\Omega$,

Test circuit

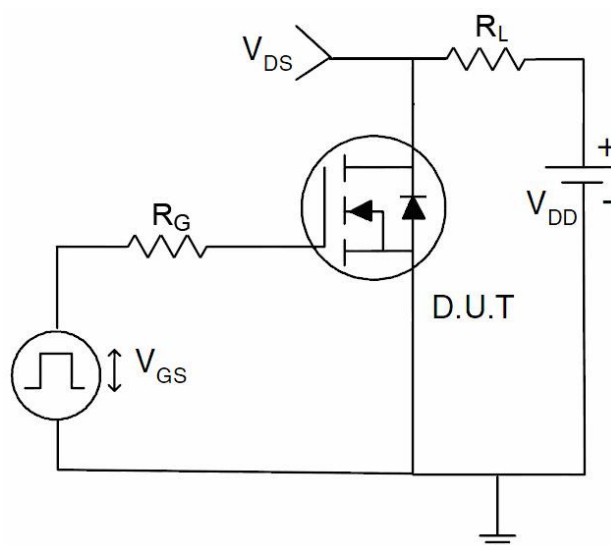
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

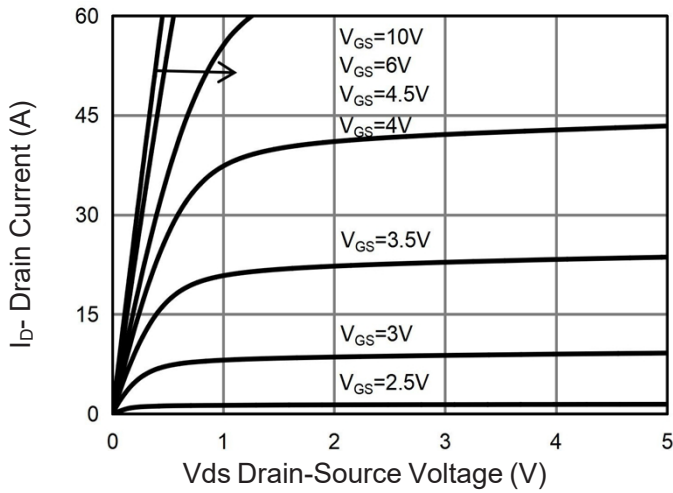


Figure 1 Output Characteristics

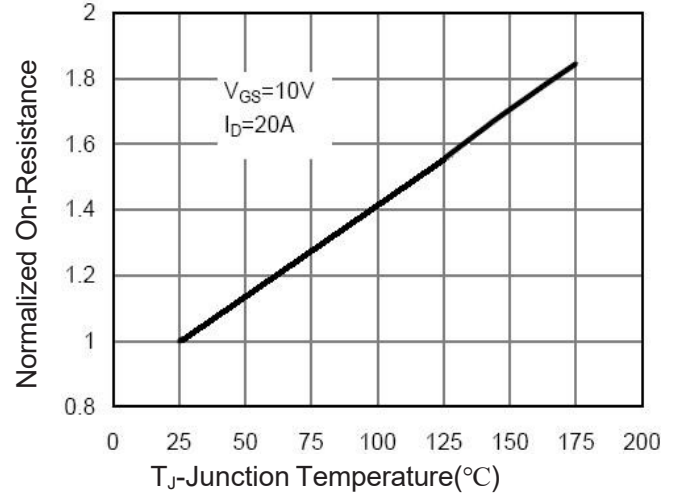


Figure 4 Rdson-Junction Temperature

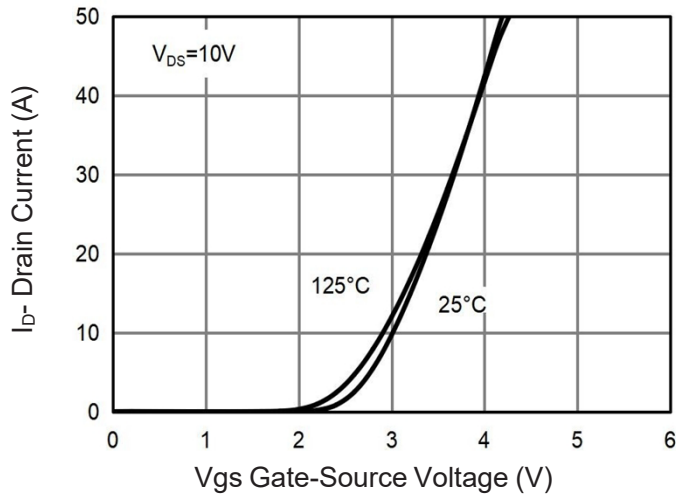


Figure 2 Transfer Characteristics

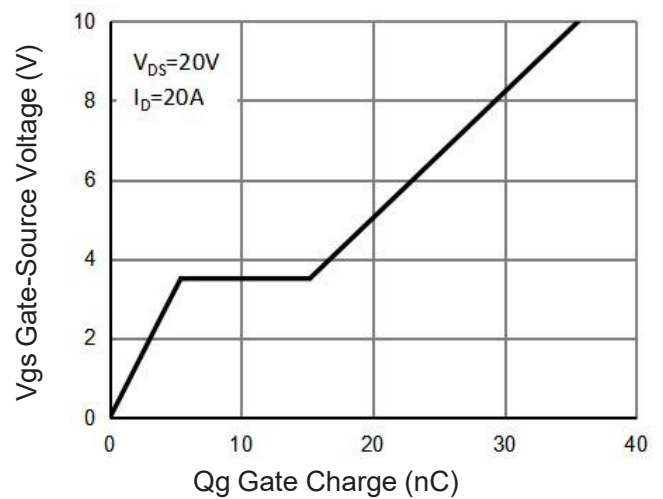


Figure 5 Gate Charge

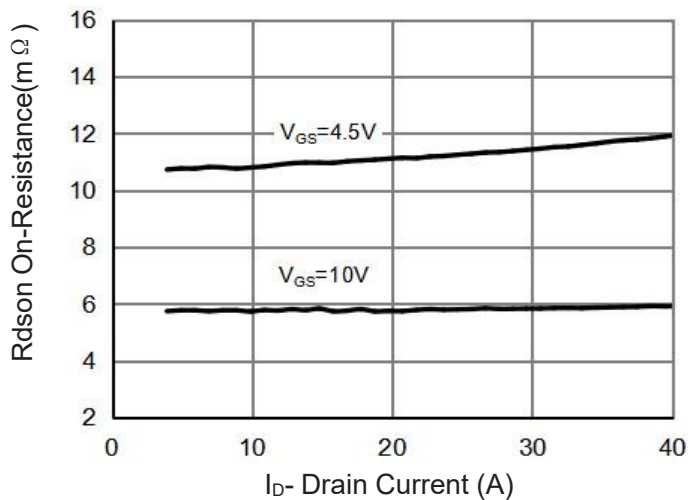


Figure 3 Rdson- Drain Current

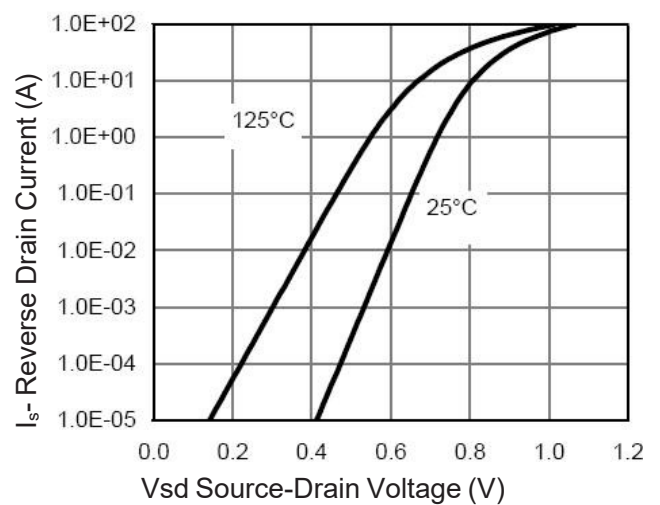
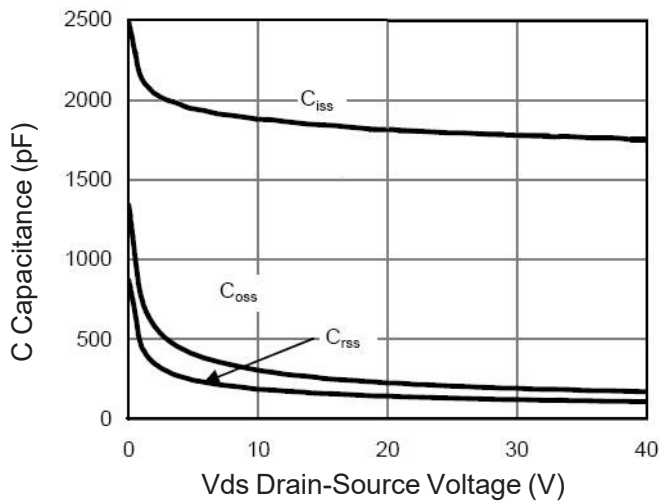
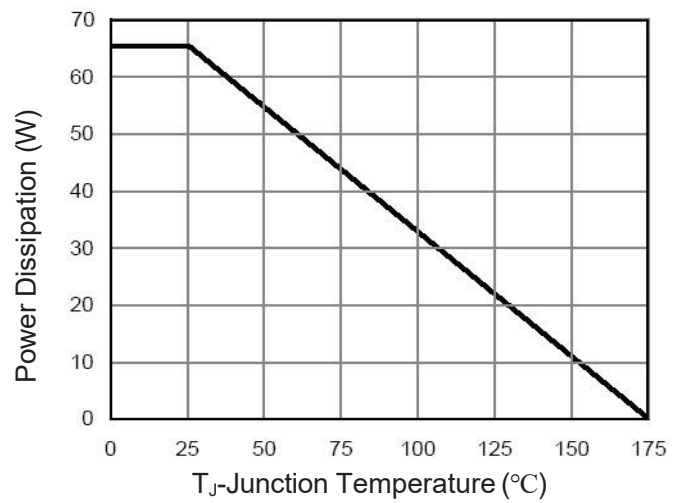
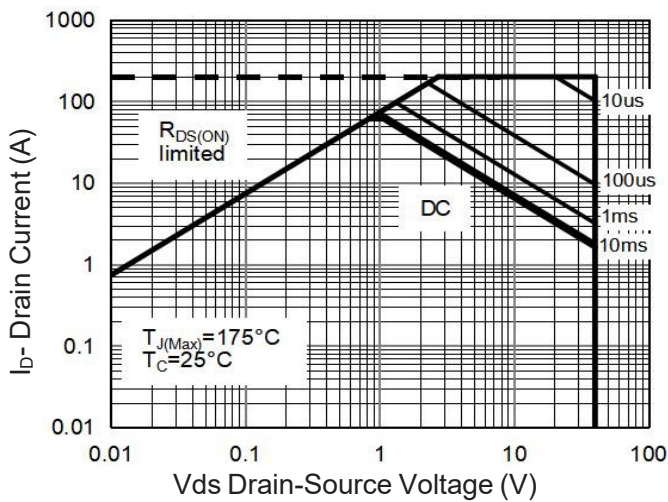
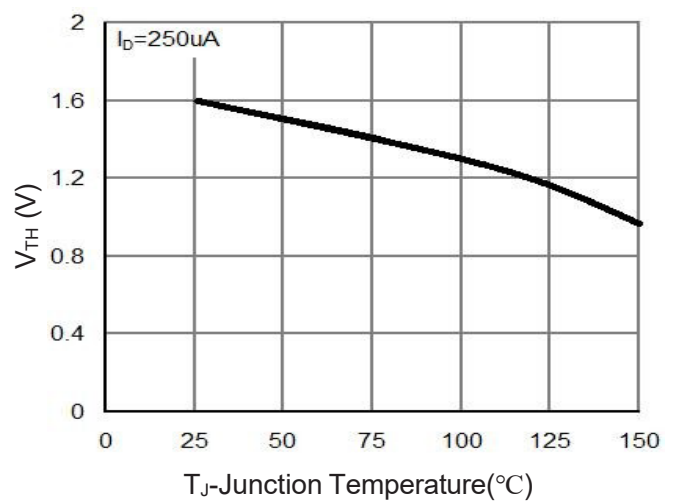
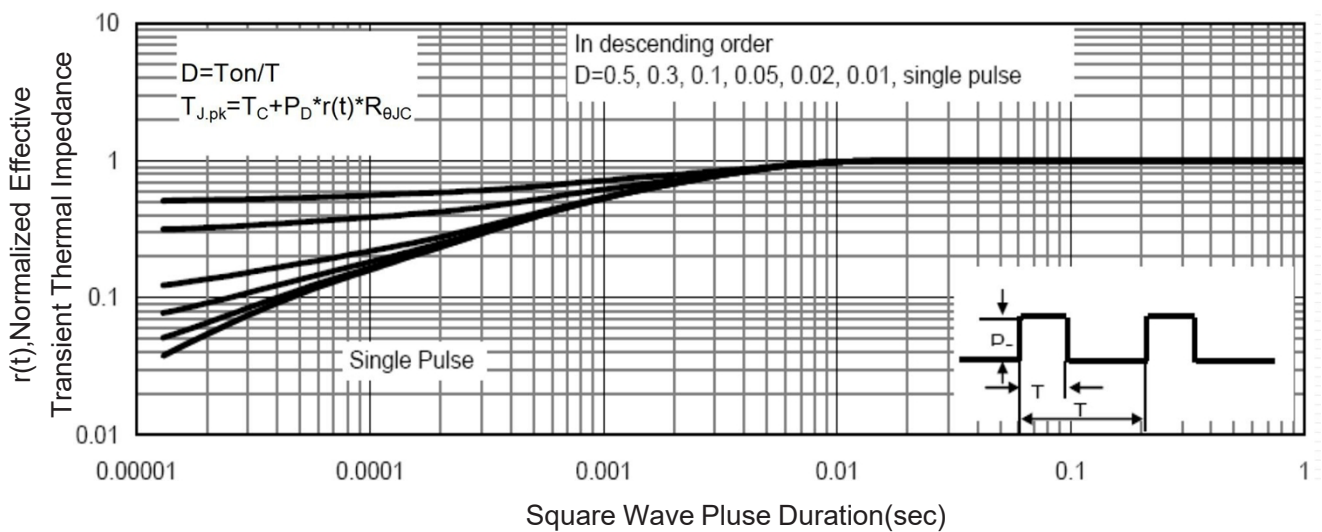


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 $V_{GS(th)}$ vs Junction Temperature

Figure 11 Normalized Maximum Transient Thermal Impedance